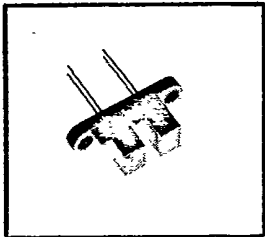


# SLOTTED OPTICAL SWITCHES PHOTOTRANSISTOR OUTPUT

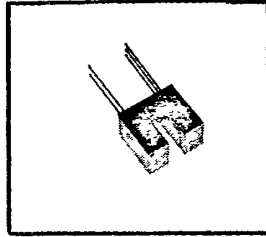


Optek Technology, Inc.  
345 Industrial Blvd.  
McKinney, Texas 75069  
(214) 542-9461

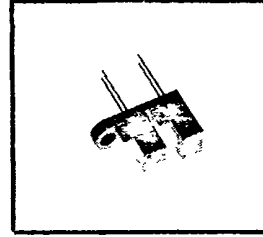
## KT 860/870/880/890 SERIES



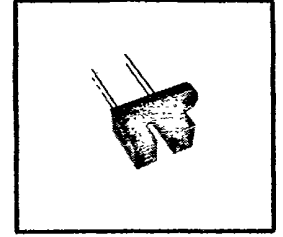
PACKAGE T



PACKAGE N



PACKAGE L

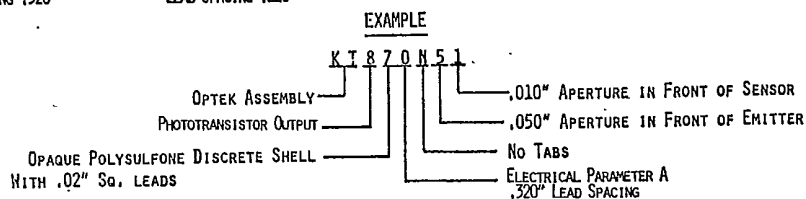
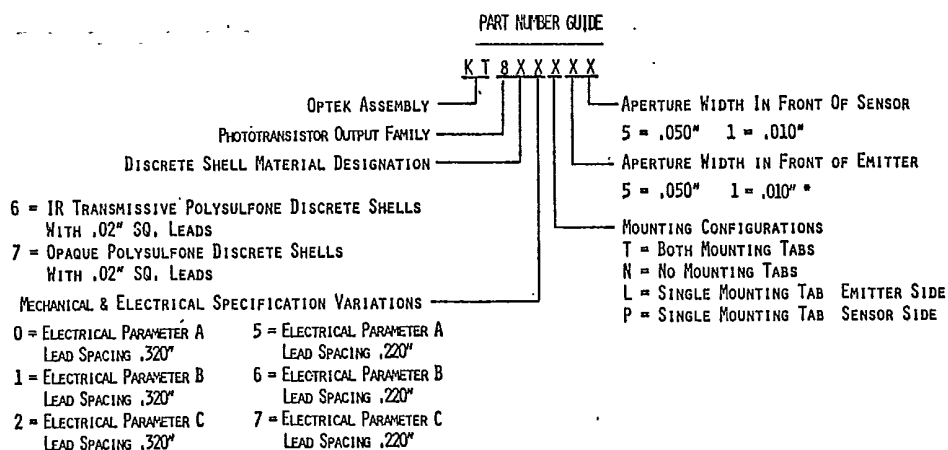


PACKAGE P

### DESCRIPTION

The KT860/KT870 series of slotted optical switches provides the design engineer with the flexibility of a custom device from a standard product line. Building from a standard housing of .125" wide slot, the user can specify (1) Electrical output parameters, (2) Mounting tab configuration, (3) Lead spacing, (4) Discrete shell, and (5) Aperture widths.

All housings are an opaque grade of injection-molded polysulfone (P1700-935) to minimize the assembly's sensitivity to ambient radiation, both visible and near-infrared. Discrete shells (exposed only on the parallel faces inside the device throat) are either IR transmissive polysulfone (P1700-1615) for applications where aperture contamination may occur, or opaque polysulfone where maximum protection against ambient radiation is a concern.



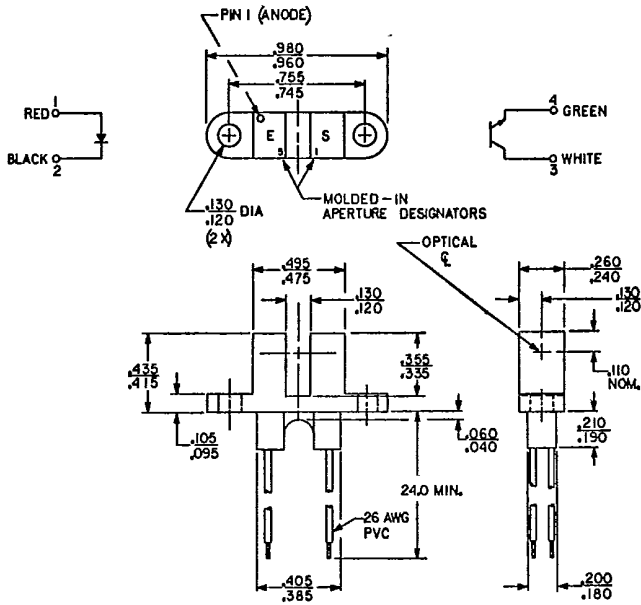
\* ASSEMBLIES WITH DUAL .010" APERTURES ARE CURRENTLY AVAILABLE WITH ELECTRICAL PARAMETER "A" ONLY.



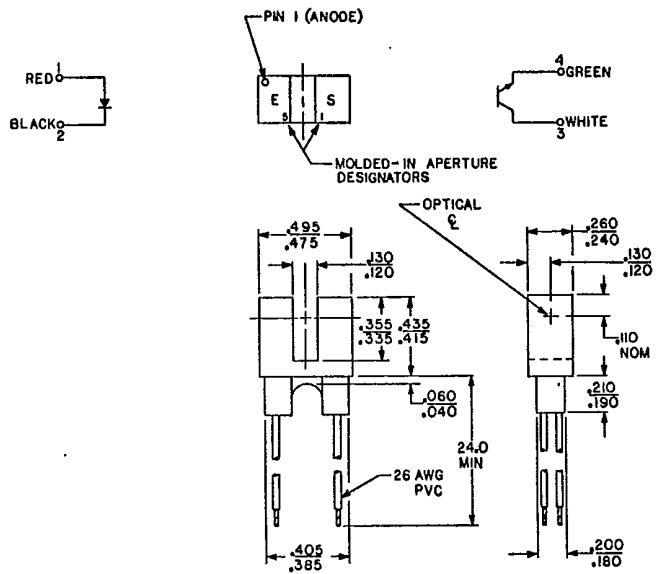


# PACKAGE CONFIGURATION

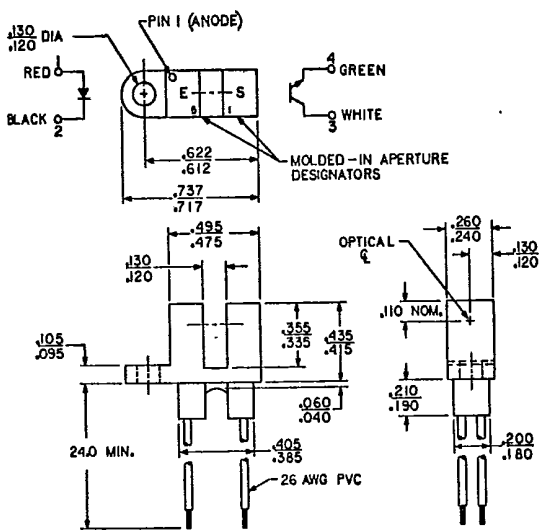
## PACKAGE T



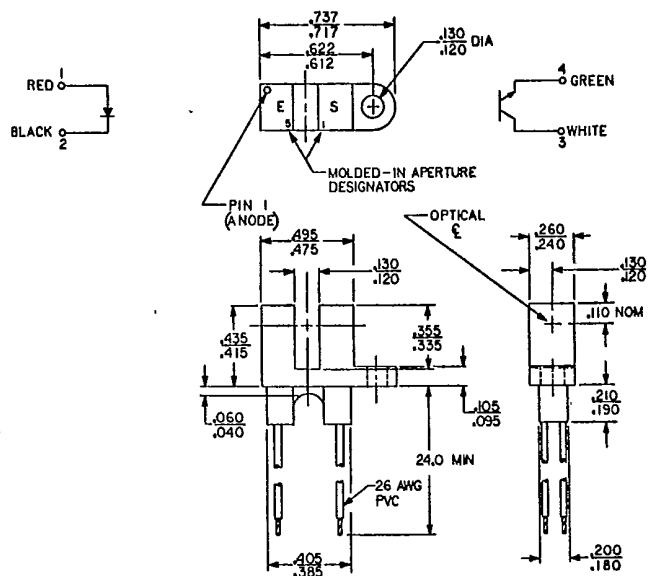
## PACKAGE N



## PACKAGE L



## PACKAGE P



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**TYPES KT860/KT870/KT880/KT890 SERIES**

ELECTRICAL CHARACTERISTICS (25°C UNLESS OTHERWISE NOTED)

| SYMBOL                        | PARAMETER   | MIN  | MAX | UNITS         | TEST CONDITIONS                               |
|-------------------------------|---|------|-----|---------------|---|
| <b>INPUT DIODE</b>            |   |      |     |               |   |
| $V_F$                         | FORWARD VOLTAGE   |      | 1.7 | V             | $I_F = 20 \text{ mA}$                         |
| $I_R$                         | REVERSE CURRENT   |      | 100 | $\mu\text{A}$ | $V_R = 3 \text{ V}$                           |
| <b>OUTPUT PHOTOTRANSISTOR</b> |   |      |     |               |   |
| $V_{(BR)CEO}$                 | COLLECTOR-EMITTER BREAKDOWN VOLTAGE   | 30   |     | V             | $I_C = 1 \text{ mA}$                          |
| $V_{(BR)ECO}$                 | EMITTER-COLLECTOR BREAKDOWN VOLTAGE   | 5    |     | V             | $I_E = 100 \mu\text{A}$                       |
| $I_{CEO}$                     | COLLECTOR-EMITTER DARK CURRENT  |      | 100 | nA            | $V_{CE} = 10 \text{ V}$                       |
| <b>COUPLED</b>                |   |      |     |               |   |
| $V_{CE} \text{ (SAT)}$        | COLLECTOR-EMITTER SATURATION VOLTAGE<br>PARAMETER A-KT860,KT865,KT870,KT875,<br>KT880,KT890 |      | 0.4 | V             | $I_C = 400 \mu\text{A}, I_F = 20 \text{ mA}$  |
|                               | PARAMETER B-KT861,KT866,KT871,KT876,<br>KT881,KT891   |      | 0.4 | V             | $I_C = 800 \mu\text{A}, I_F = 10 \text{ mA}$  |
|                               | PARAMETER C-KT862,KT867,KT872,KT877,<br>KT882,KT892   |      | 0.6 | V             | $I_C = 1800 \mu\text{A}, I_F = 20 \text{ mA}$ |
| $I_C \text{ (ON)}$            | ON-STATE COLLECTOR CURRENT<br>PARAMETER A-KT860,KT865,KT870,KT875,<br>KT880,KT890           | 500  |     | $\mu\text{A}$ | $V_{CE} = 10 \text{ V}, I_F = 20 \text{ mA}$  |
|                               | PARAMETER B-KT861,KT866,KT871,KT876,<br>KT881,KT891   | 1000 |     | $\mu\text{A}$ | $V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}$   |
|                               | PARAMETER C-KT862,KT867,KT872,KT877,<br>KT882,KT892   | 1800 |     | $\mu\text{A}$ | $V_{CE} = 0.6 \text{ V}, I_F = 20 \text{ mA}$ |

**ABSOLUTE MAXIMUM RATINGS (25°C unless otherwise noted)**

Storage and Operating Temperature Range..... KT860/KT870 Series -40°C to +85°C (A)  
 KT880/KT890 Series -40°C to +80°C (B)  
 Lead Soldering Temperature (1/16 inch from case .....+240°C (C)  
 for 5 sec. with soldering iron)

**INPUT DIODE**

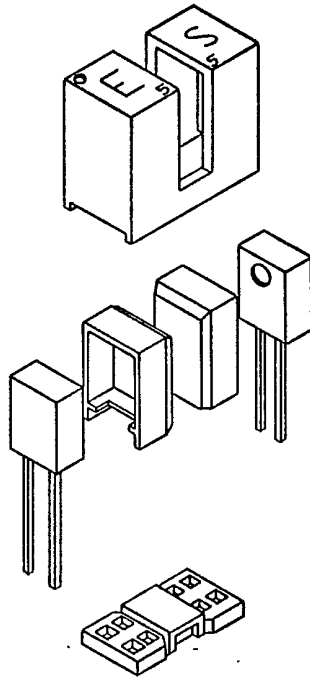
Forward DC Current.....50 mA  
 Peak Forward Current ( 1  $\mu\text{s}$  pulse width, 300pps).....3 A  
 Reverse DC Voltage.....3 V  
 Power Dissipation.....100 mW (A) (B)

**OUTPUT PHOTOTRANSISTOR**

Collector-Emitter Voltage .....30 V  
 Emitter-Collector Voltage.....5 V  
 Collector DC Current.....30 mA (A) (B)  
 Power Dissipation.....100 mW

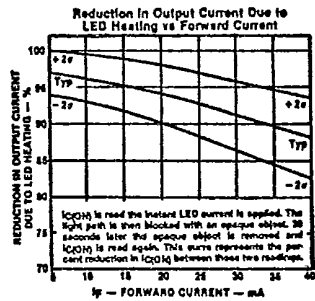
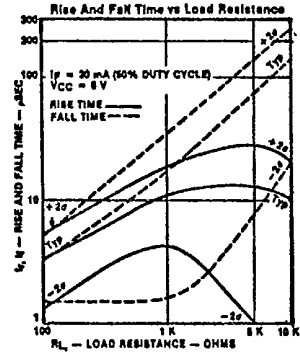
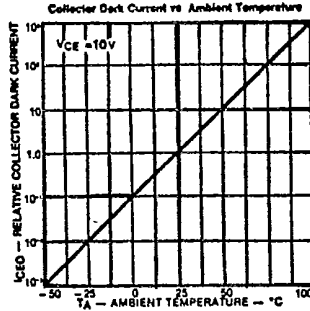
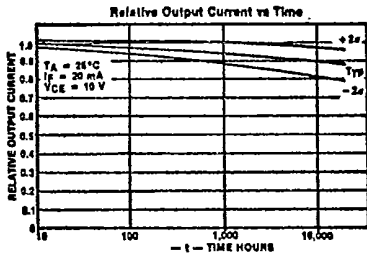
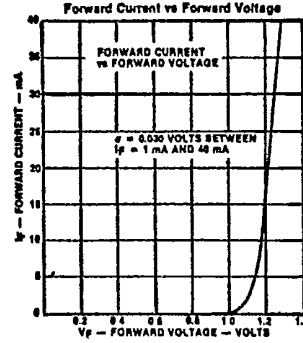
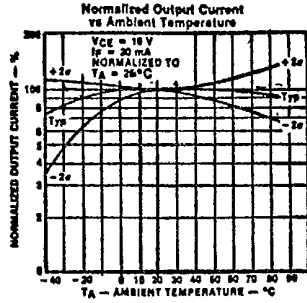
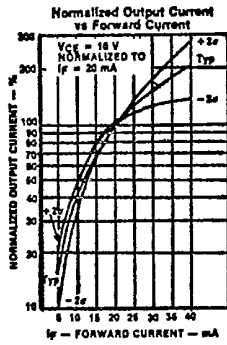
- NOTES:** (A) Derate linearly 1.67mW/°C above 25°C  
 (B) Derate linearly 1.82mW/°C above 25°C (Maximum storage and operating temperature limited by temperature rating of lead wires)  
 (C) Applies to KT860/KT870 Series only. RMA flux is recommended. Duration can be extended to 10 sec. max. when wave soldering.  
 (D) All parameters tested using pulse technique.

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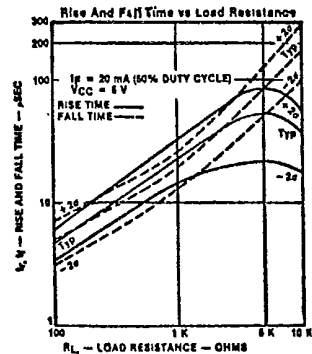
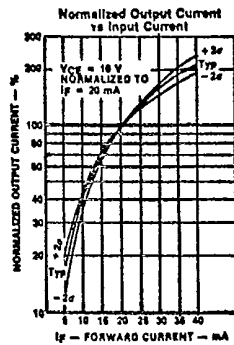


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# TYPICAL PERFORMANCE CURVES



All Part Numbers Ending In "1"



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